

EAST - [10677221.wsp:1]

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1.1: (5) gate with (silicide or salicide) with metalizing with (heat or heats or heated or heating...
1.2: (38/5/23/5) @ad<"20021119"
1.3: (5) 1 and 5
1.4: (3) 1 and 2
1.5: (51/1+7) nitrogen
1.6: (1) 4 and 5
1.7: (2) 4 not 6
1.8: (2) 1 not 4
1.9: (1) 5 and 8
1.10: (11/2) gate with (silicide or salicide) with (heat or heats or heated or heating) with (N or...
1.11: (25) 2 and 10
1.12: (10) gate with (silicide or salicide) with (heat or heats or heated or heating) with (N or...
1.13: (7) 2 and 10

US 20030032284 A1
US 6787446 B2
US 6187063 A

U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Retrieval Class	Inventor	S	C	P	1
1		US 20030032284 A1	20030213	46	Fabrication method of semiconductor integrated circuit dev	438/687	257/E21.252; 257/E21.256;		Enomoto, Hiroyuki et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
2		US 6787446 B2	20040907	NA	Fabrication method of semiconductor integrated circuit dev	438/623	257/E21.252; 257/E21.256;		Enomoto, Hiroyuki et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
		US 6187063 A	20001205	NA	MOS field effect transistor with an improved light doped diffusion layer	257/344	257/408; 257/E21.435;		Iboshi, Naoki	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>

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